

NPN RF POWER TRANSISTOR

DESCRIPTION:

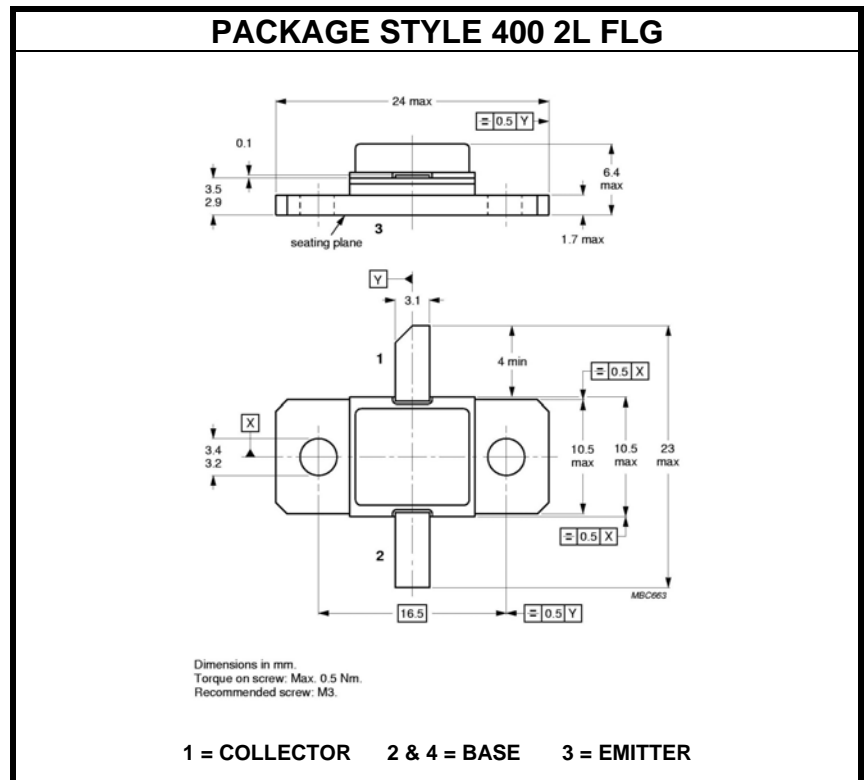
The **AM82731-050** is a Common Base Device Designed for Pulsed S-Band Pulse output and driver Applications.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	4.0 A
V_{CC}	46 V
P_{DISS}	100 W @ T _C ≤ 50 °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 15 mA	55			V
BV_{CER}	I _C = 15 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 2.0 mA	3.5			V
I_{CES}	V _{CE} = 40 V			10	mA
h_{FE}	V _{CE} = 5 V I _C = 1.5 A	30			---
P_{OUT}	V _{CC} = 40 V P _{IN} = 12.5 W f = 2.7 to 3.1 GHz	50	56		W
η_C		30	35		%
P_G		6.0	6.5		dB

Note: Pulse Width = 100 μS
Duty Cycle = 10%